

80V NPN SMALL SIGNAL TRANSISTOR IN SOT323

Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of automotive applications.

Features

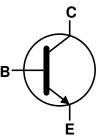
- BV_{CEO} > 80V
- I_C = 500mA Collector Current
- Epitaxial Planar Die Construction
- Ultra-Small Surface Mount Package
- Complementary PNP Type: MMSTA56Q
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

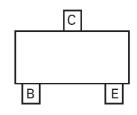
- Case: SOT323
- Case Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.006 grams (Approximate)







Device Symbol



Pin-Out Top View

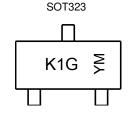
Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
MMSTA06Q-7-F	Automotive	K1G	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



K1G = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: D = 2016)

M or \overline{M} = Month (ex: 9 = September)

Date Code Key

- 410 0000	24.0 0040 1.0)												
Year	2010	6 2	2017	2018	2019	2020	2021	202	2 20	23 2	2024	2025	2026
Code	D		E	F	G	Н		J	ŀ	(L	М	N
Mont	h	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	,	1	2	3	4	5	6	7	8	9	0	N	D



Absolute Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	4	V
Collector Current	Ic	500	mA

Thermal Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P_{D}	200	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

Thermal Characteristics and Derating Information

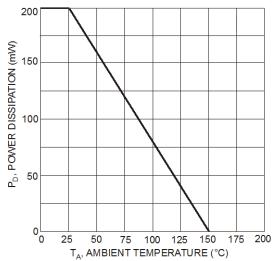


Fig. 1 Max Power Dissipation vs. Ambient Temperature

^{6.} For a device mounted with the collector lead on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is

measured under still air conditions whilst operating in a steady-state.
7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Electrical Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 8)							
Collector-Base Breakdown Voltage	BV _{CBO}	80	_	V	$I_C = 100\mu A$		
Collector-Emitter Breakdown Voltage	BV _{CEO}	80	_	V	I _C = 1mA		
Emitter-Base Breakdown Voltage	BV _{EBO}	4	_	V	$I_E = 100\mu A$		
Collector Base Cutoff Current	I _{CBO}		100	nΑ	$V_{CB} = 80V, T_A = +125^{\circ}C$		
Collector Cutoff Current	Ices		100	nA	V _{CE} = 80V		
ON CHARACTERISTICS (Note 8)							
DC Current Gain	ent Gain her 100 —			$I_C = 10 \text{mA}, V_{CE} = 1.0 \text{V}$			
Do Guiterit Gairi	h _{FE}	100		_	$I_C = 100 \text{mA}, V_{CE} = 1.0 \text{V}$		
Collector-Emitter Saturation Voltage	V _{CE(SAT)}		0.25	V	$I_C = 100 \text{mA}, I_B = 10 \text{mA}$		
Base-Emitter Saturation Voltage	V _{BE(SAT)}	_	1.2	V	$I_C = 100 \text{mA}, V_{CE} = 1.0 \text{V}$		
SMALL SIGNAL CHARACTERISTICS							
Current Gain-Bandwidth Product	f _T	100	_	MHz	V _{CE} = 2.0V, I _C = 10mA, f = 100MHz		

Note: 8. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

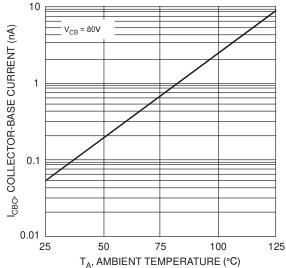


Fig. 2 Typical Collector-Cutoff Current vs. Ambient Temperature

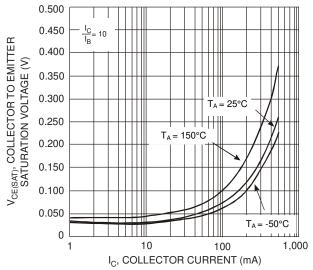


Fig. 4 Collector Emitter Saturation Voltage vs. Collector Current

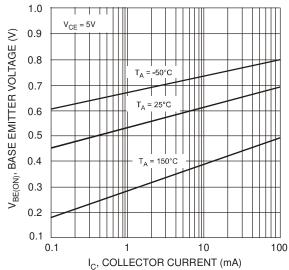


Fig. 6, Base Emitter Voltage vs. Collector Current

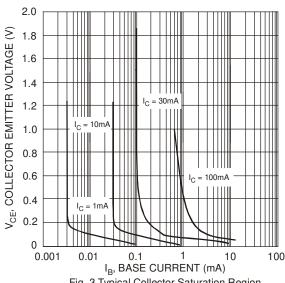


Fig. 3 Typical Collector Saturation Region

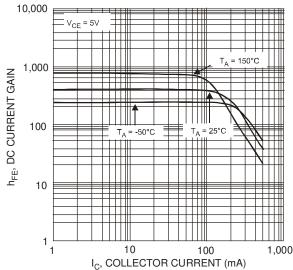


Fig. 5, DC Current Gain vs. Collector Current

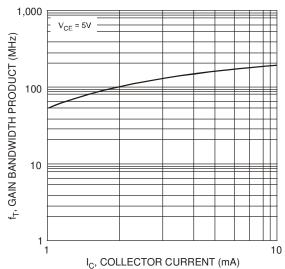
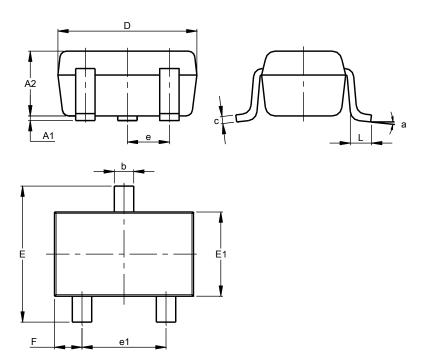


Fig. 7, Gain Bandwidth Product vs Collector Current



Package Outline Dimensions

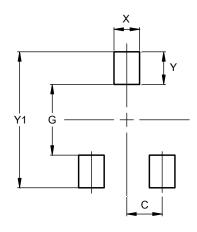
 $Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$



SOT323							
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.90	1.00	0.95				
b	0.25	0.40	0.30				
С	0.10	0.18	0.11				
D	1.80	2.20	2.15				
E	2.00	2.20	2.10				
E1	E1 1.15		1.30				
е	C).650 B	SC				
e1	1.20	1.40	1.30				
F	0.375	0.475	0.425				
L	0.25	0.40	0.30				
а	a 0° 8°						
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.470
Y	0.600
V1	2 500



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